



SHEET 1 OF 1

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Substitute for form 1449/PTO)			ATTY. DOCKET NO. 071971-0724	SERIAL NO. 10/591,597		
			APPLICANT Tohru YAMAOKA, et al.			
			FILING DATE September 05, 2006	GROUP 2614		
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ₂ (<i>if known</i>)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document		
	US	4,142,073	02-27-1979	AGNEUS et al.		
	US	2002/0181725 A1	12-05-2002	JOHANNSEN et al.		
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FOREIGN PATENT DOCUMENTS						
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number &- Kind Codes (<i>if known</i>)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation Yes No
		JP 2002-209298	07-26-2002	SEIKO EPSON CORP.		JAPAN (w/ English Abstract)
		JP 09-283373	10-31-1997	MATSUSHITA ELECTRIC WORKS LTD.		JAPAN (w/ English Abstract)
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)						
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				
		European Search Report issued in European Patent Application No. EP 04818870.0-1235/1686599 PCT/JP2004/016835, dated March 13, 2009.				
		United States Office Action issued in United States Patent Application No. 10/591,456, dated January 29, 2009.				
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		T. Majamaa et al., "Effect of Oxidation Temperature of the Electrical Characteristics of Ultrathin Silicon Dioxide Layers Plasma Oxidized in Ultrahigh Vacuum," <i>Physica Scripta</i> , Vol. T79, pp. 259-262, 1999.				
		E.C. Ross et al., "Effects of Silicon Nitride Growth Temperature on Charge Storage in the MNOS Structure," <i>Applied Physics Letters</i> , 1969, Volume 15, Number 12, pp. 408-409.				
EXAMINER			DATE CONSIDERED			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered.
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